



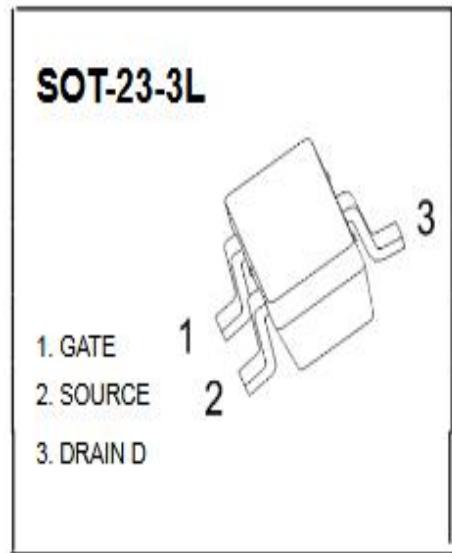
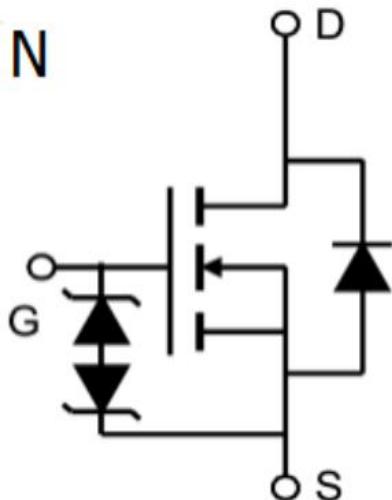
SHENZHEN MENGKE ELECTRONICS TECHNOLOGY CO.,LTD

SOT-23-3L Plastic-Encapsulate MOSFETS**MK3416****N-Channel 20-V(D-S) MOSFET**

| V(BR)DSS | RDS(on)MAX | ID |
|----------|-------------|------|
| 20 V | 20mΩ @ 4.5V | 6.5A |
| | 25mΩ @ 2.5V | |
| | 30mΩ @ 1.8V | |

FEATURE

※ TrenchFET Power MOSFET

APPLICATION※ Load Switch for Portable Devices
※ DC/DC Converter**MARKING****Equivalent Circuit****Maximum ratings (Ta=25°C unless otherwise noted)**

| Parameter | Symbol | Value | Unit |
|--|------------------|----------|------|
| Drain-Source Voltage | VDS | 20 | V |
| Gate-Source Voltage | VGS | ±8 | |
| Continuous Drain Current | ID | 6.5 | A |
| Pulsed Diode Current | IDM | 15 | |
| Continuous Source-Drain Current(Diode Conduction) | IS | 0.8 | |
| Power Dissipation | PD | 1.4 | W |
| Thermal Resistance from Junction to Ambient (t≤5s) | R _{θJA} | 125 | °C/W |
| Operating Junction | T _J | 150 | °C |
| Storage Temperature | T _{STG} | -55~+150 | °C |



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MOSFET ELECTRICAL CHARACTERISTICS

Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)

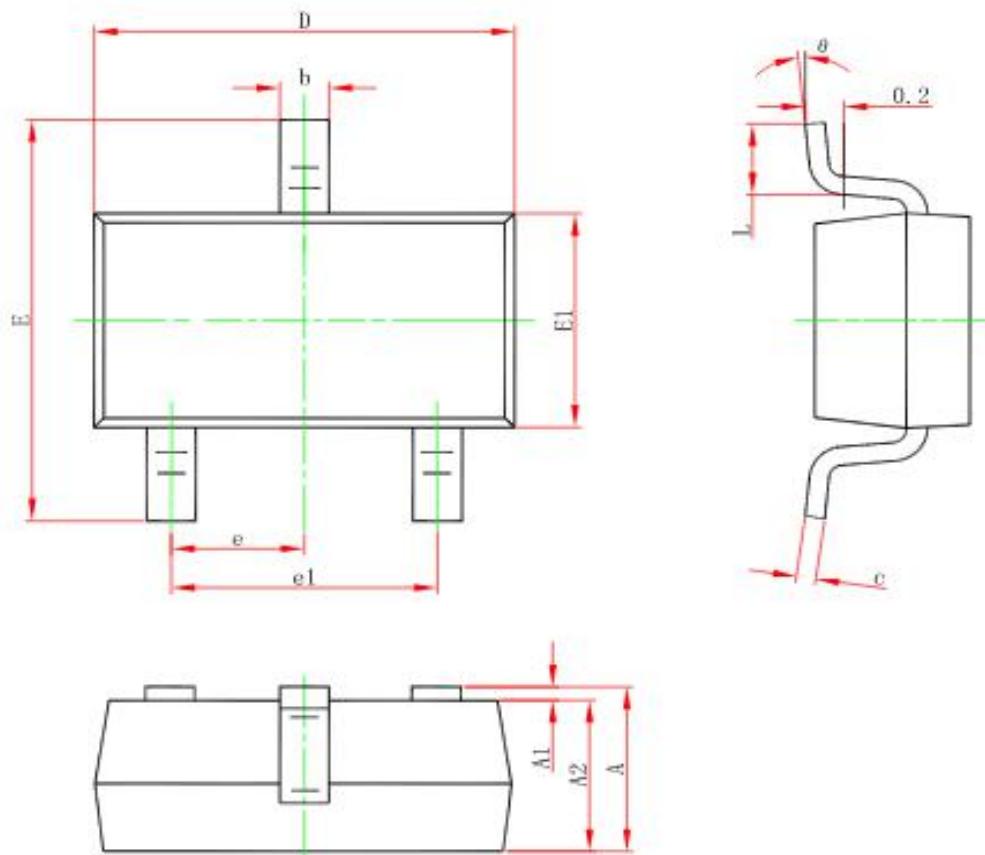
| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|--|----------|--|-----|------|-------|------|
| Static | | | | | | |
| Drain-source breakdown voltage | V(BR)DSS | VGS = 0V, ID = 250μA | 20 | | | V |
| Gate-source threshold voltage | VGS(th) | VDS = VGS, ID = 250μA | 0.4 | | 1.1 | V |
| Gate-source leakage | IGSS | VDS = 0V, VGS = ±8V | | | ±10 | μA |
| Zero gate voltage drain current | IDSS | VDS = 20V, VGS = 0V | | | 1 | μA |
| Drain-source on-state resistancea | RDS(on) | VGS = 4.5V, ID = 4A | | 17 | 20 | mΩ |
| | | VGS = 2.5V, ID = 2A | | 20 | 25 | mΩ |
| | | VGS = 1.8V, ID = 1A | | 25 | 34 | mΩ |
| Forward transconductancea | gfs | VDS = 4.5V, ID = 4A | | 20 | | S |
| Diode forward voltage | VSD | IS=1.6A, VGS=0V | | 0.7 | 1.3 | V |
| Dynamic | | | | | | |
| Input capacitance | Ciss | VDS = 10V, VGS = 0V, f=1MHz | | 1160 | | pF |
| Output capacitance | Coss | | | 104 | | pF |
| Reverse transfer capacitanceb | Crss | | | 29 | | pF |
| Total gate charge | Qg | VDS = 10V, VGS = 4.5V, ID = 4A | | 10 | 13 | nC |
| Gate-source charge | Qgs | | | 1.4 | 1.82 | nC |
| Gate-drain charge | Qgd | | | 2.7 | 3.51 | nC |
| Gate resistance | Rg | f=1MHz | | 6 | | Ω |
| Switchingb | | | | | | |
| Turn-on delay time | td(on) | VDD= 10V RL=1.5Ω, ID ≈ 1A, VGEN= 4.5V, Rg=3Ω | | 6.2 | 12.4 | ns |
| Rise time | tr | | | 12.7 | 25.4 | ns |
| Turn-off delay time | td(off) | | | 51.7 | 103.4 | ns |
| Fall time | tf | | | 16 | 32 | ns |
| Drain-source body diode characteristics | | | | | | |
| Continuous Source-Drain Diode Current | IS | Tc=25°C | | | 3.2 | A |

Note :

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.



SOT-23-3L PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E | 1.500 | 1.700 | 0.059 | 0.067 |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| theta | 0° | 8° | 0° | 8° |